

SAMTM Data Sheet SAM-1064-1-10ps-x, λ = 1064 nm

High reflection band λ = 1000 1085 nmAbsorbance A_0 = 1 %Modulation depth ΔR = 0.6 %Non-saturable loss A_{ns} = 0.4 %			
Modulation depth $\Delta R = 0.6 \%$			
Non-saturable loss $A_{ns} = 0.4 \%$			
Saturation fluence $\Phi_{sat} = 70 \ \mu J/cm^2$			
Relaxation time constant $\tau \sim 10 \text{ ps}$			
Damage threshold $\Phi = 3 \text{ mJ/cm}^2$			
Chip area 4.0 mm x 4.0 mm; other dimensions on request			
Chip thickness 450 µm			
Protection the SAM is protected with a dielectric front layer			
Mounting option x denotes the type of mounting as follows: x = 0 unmounted x = 12.7 g glued on a gold plated Cu-cylinder with 12.7 mm Ø			

x = 12.7 g	glued on a gold plated Cu-cylinder with 12.7 mm $arnothing$
x = 25.4 g	glued on a gold plated Cu-cylinder with 25.4 mm $arnothing$
x = 12.7 s	soldered on a gold plated Cu-cylinder with 12.7 mm $arnothing$
x = 25.4 s	soldered on a gold plated Cu-cylinder with 25.4 mm $arnothing$
x = 25.4 w x = FC	soldered on a water cooled Cu-cylinder with 25.4 mm \varnothing mounted on a 1 m monomode fiber cable with FC connector
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Low intensity spectral reflectance





